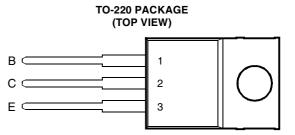
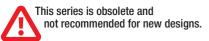
BOURNS®

BDX53, BDX53A, BDX53B, BDX53C NPN SILICON POWER DARLINGTONS

- Designed for Complementary Use with BDX54, BDX54A, BDX54B and BDX54C
- 60 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A





Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDX53		45		
Collector-base voltage ($I_E = 0$)	BDX53A	V	60	v	
	BDX53B	Усво	80	v	
	BDX53C		100		
Collector-emitter voltage (I _B = 0)	BDX53		45		
	BDX53A	V	60	V	
	BDX53B	V _{CEO}	80		
	BDX53C		100		
Emitter-base voltage		V _{EBO}	5	V	
Continuous collector current		Ι _C	8	А	
Continuous base current		I _B	0.2	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)	P _{tot}	60	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note	P _{tot}	2	W		
Operating junction temperature range	Тj	-65 to +150	°C		
Operating temperature range		T _{stg}	-65 to +150	°C	
Operating free-air temperature range		T _A	-65 to +150	°C	

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.48 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

BDX53, BDX53A, BDX53B, BDX53C NPN SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS				MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	l _C = 100 mA	I _B = 0	(see Note 3)	BDX53 BDX53A BDX53B BDX53C	45 60 80 100			V
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = 30 V$ $V_{CE} = 30 V$ $V_{CE} = 40 V$ $V_{CE} = 50 V$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDX53 BDX53A BDX53B BDX53C			0.5 0.5 0.5 0.5	mA
I _{CBO}	Collector cut-off current	$V_{CB} = 45 V$ $V_{CB} = 60 V$ $V_{CB} = 80 V$ $V_{CB} = 100 V$	$I_{E} = 0$ $I_{E} = 0$ $I_{E} = 0$ $I_{E} = 0$		BDX53 BDX53A BDX53B BDX53C			0.2 0.2 0.2 0.2	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	$I_{\rm C} = 0$					2	mA
h _{FE}	Forward current transfer ratio	V _{CE} = 3 V	I _C = 3 A	(see Notes 3 and 4	4)	750			
V _{BE(sat)}	Base-emitter saturation voltage	l _B = 12 mA	I _C = 3 A	(see Notes 3 and 4	4)			2.5	V
V _{CE(sat)}	Collector-emitter saturation voltage	l _B = 12 mA	I _C = 3 A	(see Notes 3 and 4	4)			2	V
V _{EC}	Parallel diode forward voltage	I _E = 3 A	$I_{B} = 0$					2.5	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	ТҮР	MAX	UNIT
R _{0JC} Junction to case thermal resistance			2.08	°C/W
R _{0JA} Junction to free air thermal resistance			62.5	°C/W

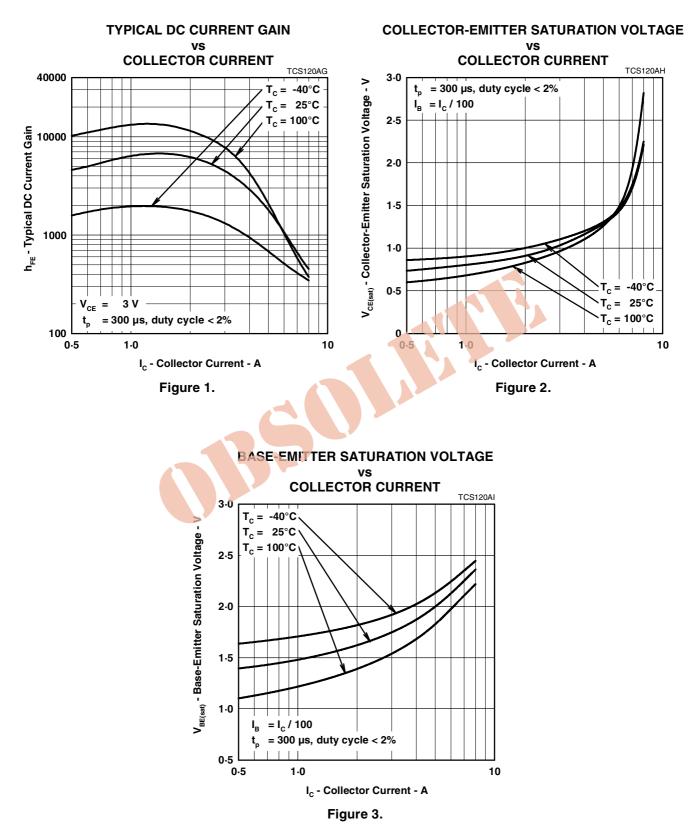
resistive-load-switching characteristics at 25°C case temperature

		PARAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t	ton	Turn-on time	I _C = 3 A	I _{B(on)} = 12 mA	$I_{B(off)} = -12 \text{ mA}$		1		μs
t	off	Turn-off time	$V_{BE(off)} = -4.5 V$	$R_L = 10 \Omega$	t_p = 20 μ s, dc \leq 2%		5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

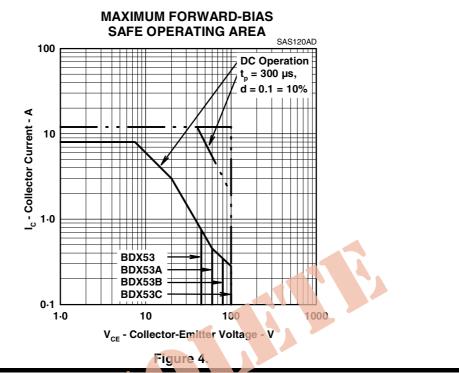


TYPICAL CHARACTERISTICS





MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION MAXIMUM POWER DISSIPATION vs **CASE TEMPERATURE** TIS120AB 80 P_{tot} - Maximum Power Dissipation - W 70 60 50 40 30 20 10 0 0 25 50 75 100 150 125 T_c - Case Temperature - °C Figure 5.

PRODUCT INFORMATION